Product Discontinued - Not for New Designs

EnerChip™ CC CBC3112

EnerChip CC with Integrated Power Management

Features

- Power Manager with Charge Control
- Integrated 12µAh Thin Film Energy Storage
- Built-in Energy Storage Protection
- Temperature Compensated Charge Control
- Adjustable Switchover Voltage
- Charges Integrated EnerChip Over a Wide Supply Range
- Low Standby Power
- SMT - Solder Reflow Tolerant
- Thousands of Recharge Cycles
- Low Self-Discharge
- Eco-Friendly, RoHS Compliant

Applications

- **Standby supply** for non-volatile SRAM, Real-time clocks, controllers, supply supervisors, and other system-critical components.
- **Wireless sensors and RFID tags** and other powered, low duty cycle applications.
- **Localized power source** to keep microcontrollers and other devices alert in standby mode.
- **Power bridging** to provide back-up power to system during exchange of main batteries.
- **Consumer appliances** that have real-time clocks; provides switchover power from main supply to backup battery.
- **Business and industrial systems** such as: network routers, point-of-sale terminals, single-board computers, test equipment, multi-function printers, industrial controllers, and utility meters.
- **Energy Harvesting** by coupling the EnerChip with energy transducers such as solar panels.

7 mm x 7 mm DFN SMT Package:

The EnerChip CC is the world's first Intelligent Thin Film Energy Storage Device. It is an integrated solution that provides backup energy storage and power management for systems requiring power bridging and/or secondary power. A single EnerChip CC can charge up to 10 additional EnerChips connected in parallel.

During normal operation, the EnerChip CC charges itself with a controlled voltage using an internal charge pump that operates from 2.5V to 5.5V. An ENABLE pin allows for activation and deactivation of the charge pump using an external control line in order to minimize current consumption and take advantage of the fast recharge time of the EnerChip.

When the primary power supply dips below a user-defined threshold voltage, the EnerChip CC will signal this event and route the EnerChip voltage to VOUT. The EnerChip CC also has energy storage protection circuitry to enable thousands of recharge cycles.

The CBC3112 is a 20-pin, 7 mm x 7 mm Dual Flat No-lead (DFN) package, available in tubes, trays, or tape-and-reel for use with automatic insertion equipment.

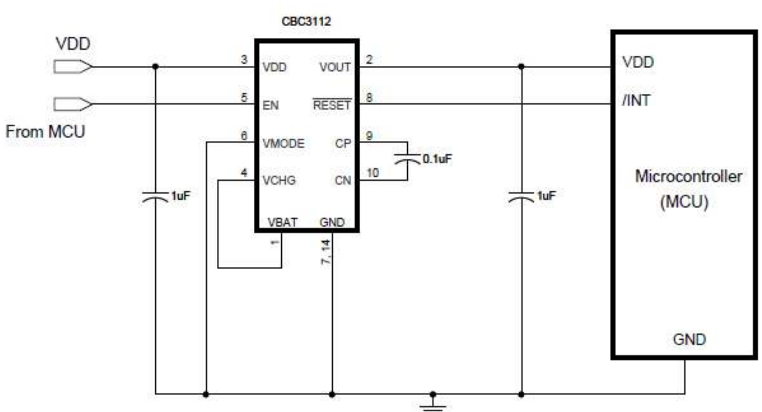


Figure 1 - Typical EnerChip CC Application Circuit

Electrical Properties

EnerChip Backup Output voltage:	3.3V
Energy Capacity (typical):	12µAh
Recharge time to 80%:	10 minutes
Charge/Discharge cycles:	>5000 to 10% discharge

Physical Properties

Package size:	7 mm x 7 mm
Operating temperature:	-20°C to +70°C
Storage temperature:	-40°C to +125°C (prior to 1st charge)

Functional Block Diagram

The EnerChip CC internal schematic is shown in Figure 2. The input voltage from the power supply (V_{DD}) is applied to the charge pump, the control logic, and is compared to the user-set threshold as determined by the voltage on V_{MODE}. V_{MODE} is an analog input ranging from 0V to V_{DD}. The ENABLE pin is a digital input that turns off the charge pump when low. V_{OUT} is either supplied from V_{DD} or the integrated EnerChip. $\overline{\text{RESET}}$ is a digital output that, when low, indicates V_{OUT} is being sourced by the integrated EnerChip.

C_{FLY} is the flying capacitor in the voltage doubler circuit. The value of C_{FLY} can be changed if the output impedance of the EnerChip CC needs to be modified. The output impedance is dictated by *1/fC*, where *f* is the frequency of oscillation (typically 100kHz) and *C* is the capacitor value (typically 0.1µF). GND is system ground.

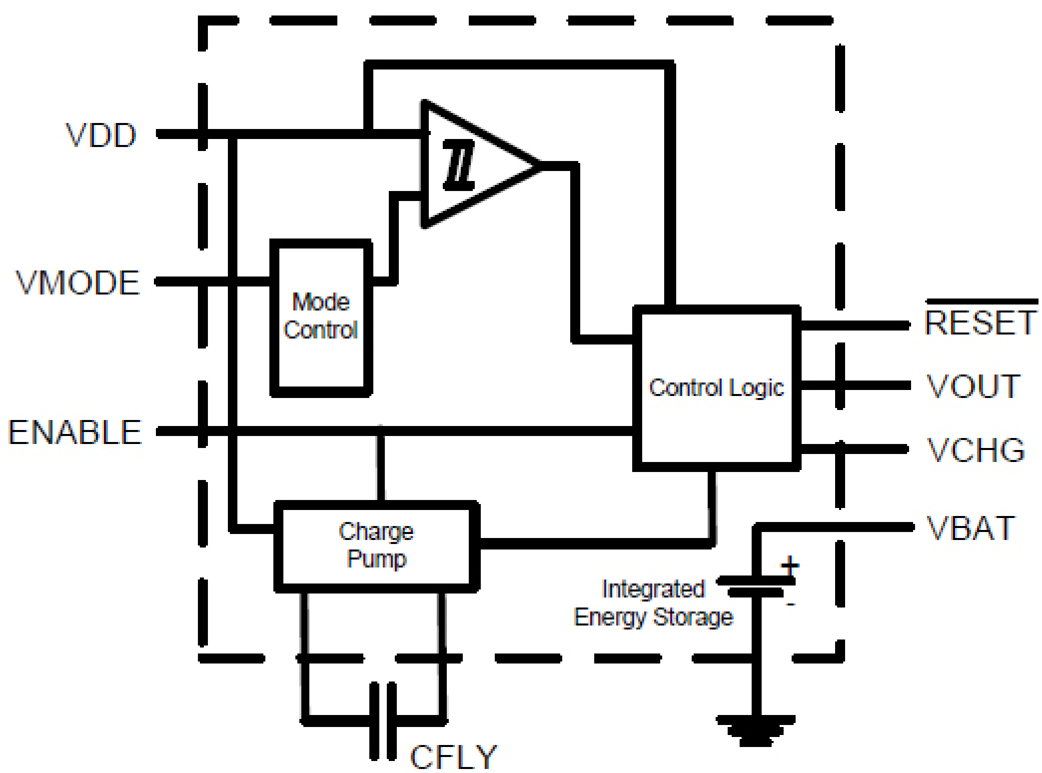


Figure 2: EnerChip CC CBC3112 Internal Block Diagram

Device Input/Ouput Descriptions

Pin Number(s)	Label	Description
1	V_{BAT}	Positive EnerChip Terminal - Tie to Pin 4
2	V_{OUT}	System Voltage
3	V_{DD}	Input Voltage
4	V_{CHG}	EnerChip Charge Voltage - Tie to Pin 1 and/or Optional EnerChip(s)
5	ENABLE	Charge Pump Enable
6	V_{MODE}	Mode Select for Backup Switchover Threshold
7	GND	System Ground
8	$\overline{RESET}$	Reset Signal (Active Low)
9	C_P	Flying Capacitor Positive
10	C_N	Flying Capacitor Negative
11	NC	No Connection
12	NC	No Connection
13	NC	No Connection
14	GND	System Ground
15	NC	No Connection
16	NC	No Connection
17	NC	No Connection
18	NC	No Connection
19	NC	No Connection
20	NC	No Connection

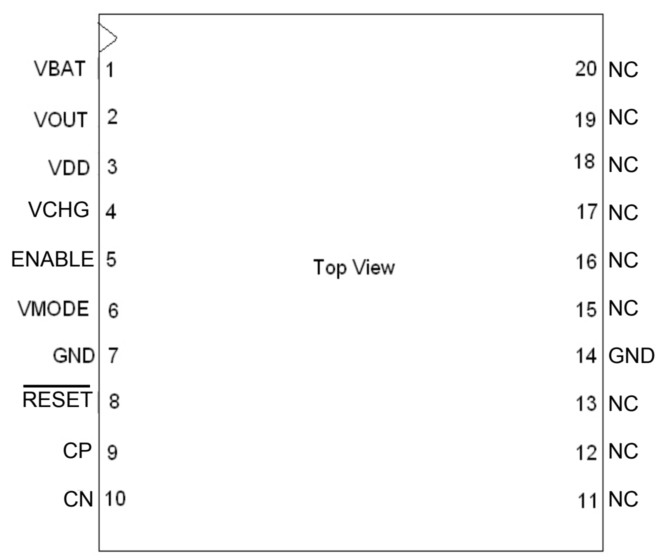


Figure 3: EnerChip CC CBC3112 Package Pin-out

Absolute Maximum Ratings

PARAMETER	CONDITION	MIN	TYPICAL	MAX	UNITS
V_{DD} with respect to GND	25°C	GND - 0.3	-	6.0	V
ENABLE and V_{MODE} Input Voltage	25°C	GND - 0.3	-	V_{DD}+0.3	V
V_{BAT} (1)	25°C	3.0	-	4.15	V
V_{CHG} (1)	25°C	3.0	-	4.15	V
V_{OUT}	25°C	GND - 0.3	-	6.0	V
$\overline{\text{RESET}}$ Output Voltage	25°C	GND - 0.3	-	V_{OUT}+0.3	V
CP, Flying Capacitor Voltage	25°C	GND - 0.3	-	6.0	V
CN	25°C	GND - 0.3	-	V_{DD}+0.3	V

(1) *No external connections to these pins are allowed, except parallel EnerChips.*

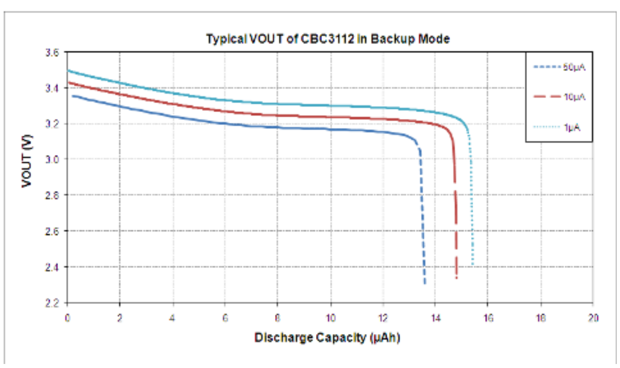
Operating Characteristics

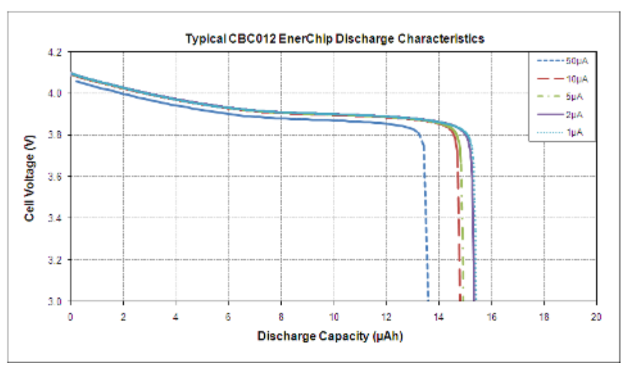
PARAMETER		CONDITION	MIN	TYPICAL	MAX	UNITS
Output Voltage V_{OUT}		V_{DD} > V_{TH}	-	V_{DD}	-	V
Output Voltage V_{OUT} (backup mode)		V_{DD} < V_{TH}	2.2	3.3	3.6	V
EnerChip Pulse Discharge Current		-	Variable - see App. Note 1025			-
Self-Discharge (5-yr. average; 25°C)		Non-recoverable	-	2.5	-	% per year
		Recoverable	-	1.5 (1)	-	% per year
Operating Temperature		-	-40 (2)	25	+70	°C
Storage Temperature		-	-40	-	+125 (3)	°C
Cell Resistance (25°C)		Charge cycle 2	-	2.15	5.35	kΩ
		Charge cycle 1000	-	10.7	21.3	
Recharge Cycles (to 80% of rated capacity; 4.1V charge voltage)	25°C	10% depth-of-discharge	5000	-	-	cycles
		50% depth-of discharge	1000	-	-	cycles
	40°C	10% depth-of-discharge	2500	-	-	cycles
		50% depth-of-discharge	500	-	-	cycles
Recharge Time (to 80% of rated capacity; 4.1V charge; 25°C)		Charge cycle 2	-	10	22	minutes
		Charge cycle 1000	-	45	70	
Capacity		50µA discharge; 25°C	12	-	-	µAh

(1) *First month recoverable self-discharge is 4% average.*

(2) *Cell resistance and charging time increase with decreasing temperature.*

(3) *Storage temperature is for EnerChip CC device before 1st charge is applied.*

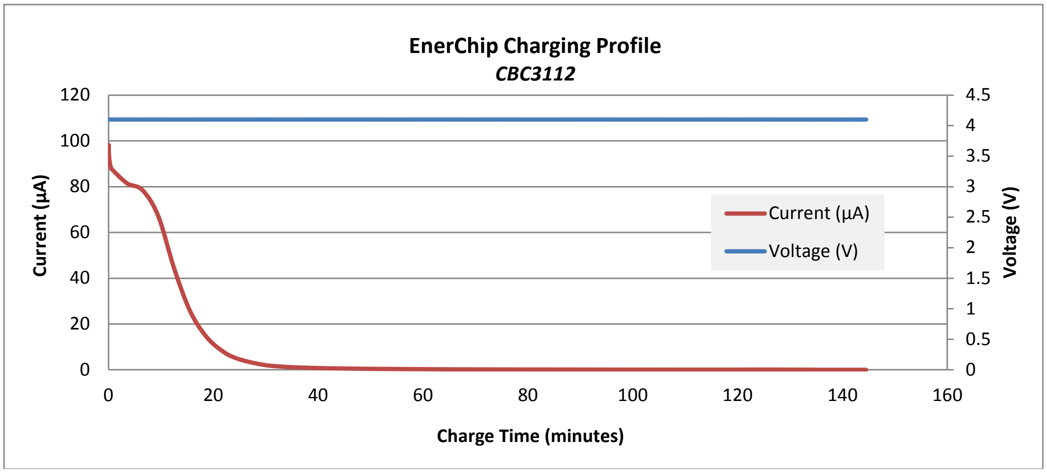


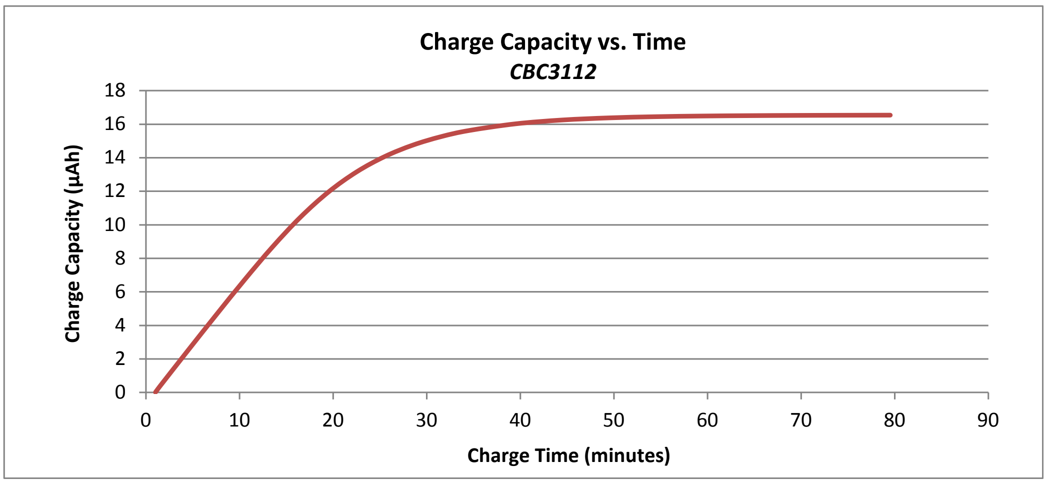


Note: All specifications contained within this document are subject to change without notice.

EnerChip Charging Characteristics

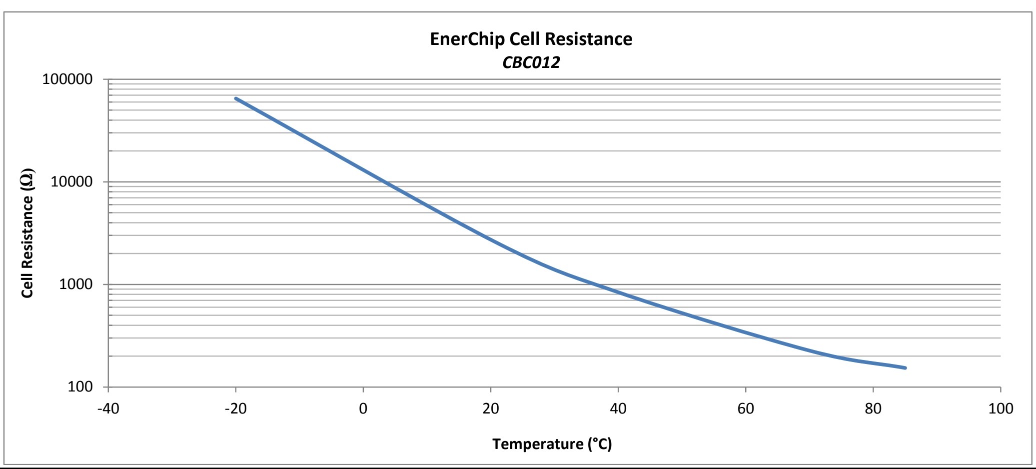
The EnerChip can be recharged quickly. The following graphs illustrate the correlation between charging time and charging current into a discharged cell, and also the cumulative charge vs. charging time. Both graphs are typical based on constant 4.1V charging at room temperature. Charging time increases at lower temperature.





EnerChip Temperature Characteristics

EnerChip cell resistance increases (decreases) with decreasing (increasing) temperature. The following graph represents typical cell resistance over the rated operating temperature range.



POWER SUPPLY CURRENT CHARACTERISTICS
Ta = -20ºC to +70ºC

CHARACTERISTIC	SYMBOL	CONDITION		MIN	MAX	UNITS
Quiescent Current	I_Q	ENABLE=GND	V_{DD}=3.3V	-	3.5	µA
			V_{DD}=5.5V	-	6.0	µA
		ENABLE=V_{DD}	V_{DD}=3.3V	-	35	µA
			V_{DD}=5.5V	-	38	µA
EnerChip Cutoff Current	$I_{QBATOFF}$	V_{BAT} < V_{BATCO}, V_{OUT}=0		-	0.5	nA
	I_{QBATON}	V_{BAT} > V_{BATCO}, ENABLE=V_{DD}, I_{OUT}=0		-	42	nA

INTERFACE LOGIC SIGNAL CHARACTERISTICS
V_{DD} = 2.5V to 5.5V, Ta = -20ºC to +70ºC

CHARACTERISTIC	SYMBOL	CONDITION	MIN	MAX	UNITS
High Level Input Voltage	V_{IH}	-	V_{DD} - 0.5	-	Volts
Low Level Input Voltage	V_{IL}	-	-	0.5	Volts
High Level Output Voltage	V_{OH}	V_{DD}>V_{TH} (see Figures 4 and 5) I_L=10µA	V_{DD} - 0.04V (1)	-	Volts
Low Level Output Voltage	V_{OL}	I_L = -100µA	-	0.3	Volts
Logic Input Leakage Current	I_{IN}	0<V_{IN}<V_{DD}	-1.0	+1.0	nA

(1) *$\overline{RESET}$ tracks V_{DD}; $\overline{RESET}$ = V_{DD} - (I_{OUT} x R_{OUT}).*

$\overline{RESET}$ SIGNAL AC/DC CHARACTERISTICS
V_{DD} = 2.5V to 5.5V, Ta = -20ºC to +70ºC

CHARACTERISTIC	SYMBOL	CONDITION	MIN	MAX	UNITS
V_{DD} Rising to $\overline{RESET}$ Rising	t_{RESETH}	V_{DD} rising from 2.8V TO 3.1V in <10µs	60	200	ms
V_{DD} Falling to $\overline{RESET}$ Falling	t_{RESETL}	V_{DD} falling from 3.1V to 2.8V in <100ns	0.5	2	µs
Mode 1 TRIP V V_{DD} Rising	V_{RESET}	V_{MODE} = GND	2.80	3.20	V
Mode 2 TRIP V (2) V_{DD} Rising	V_{RESET}	V_{MODE} = V_{DD}/2	2.25	2.60	V
$\overline{RESET}$ Hysteresis Voltage (3) (V_{DD} to $\overline{RESET}$)	V_{HYST}	V_{MODE}=V_{DD}	60	100	mV
		V_{MODE}=GND	45	75	
		V_{MODE} = V_{DD}/2	30	50	

(2) *User-selectable trip voltage can be set by placing a resistor divider from the VMODE pin to GND. Refer to Figure 8.*

(3) *The hysteresis is a function of trip level in Mode 2. Refer to Figure 9.*

CHARGE PUMP CHARACTERISTICS
V_{DD} = 2.5V to 5.5V, Ta = -20ºC to +70ºC

CHARACTERISTIC	SYMBOL	CONDITION	MIN	MAX	UNITS
ENABLE=V_{DD} to Charge Pump Active	t_{CPON}	ENABLE to 3rd charge pump pulse, V_{DD}=3.3V	60	80	µs
ENABLE Falling to Charge Pump Inactive	t_{CPOFF}	-	0	1	µs
Charge Pump Frequency	f_{CP}		-	120	KHz (1)
Charge Pump Resistance	R_{CP}	Delta V_{BAT}, for I_{BAT} charging current of 1µA to 100µA C_{FLY}=0.1µF, C_{BAT}=1.0µF	150	300	Ω
V_{CHG} Output Voltage	V_{CP}	C_{FLY}=0.1µF, C_{BAT}=1.0µF, I_{OUT}=1µA, Temp=+25ºC	4.075	4.125	V
V_{CHG} Temp. Coefficient	T_{CCP}	I_{OUT}=1µA, Temp=+25ºC	-2.0	-2.4	mV/ºC
Charge Pump Current Drive	I_{CP}	I_{BAT}=1mA C_{FLY}=0.1µF, C_{BAT}=1.0µF	1.0	-	mA
Charge Pump on Voltage	V_{ENABLE}	ENABLE=V_{DD}	2.5	-	V

(1) *$f_{CP} = 1/t_{CPPER}$*

ADDITIONAL CHARACTERISTICS
Ta = -20ºC to +70ºC

CHARACTERISTIC	SYMBOL	CONDITION	LIMITS		UNITS
			MIN	MAX	
V_{BAT} Cutoff Threshold	V_{BATCO}	I_{OUT}=1µA	2.75	3.25	V
Cutoff Temp. Coefficient	T_{CCO}	-	+1	+2	mV/ºC
V_{BAT} Cutoff Delay Time	t_{COOFF}	V_{BAT} from 40mV above to 20mV below V_{BATCO} I_{OUT}=1µA	18	-	ms
V_{OUT} Dead Time, V_{DD} Rising (2)	t_{RSBR}	I_{OUT}=1mA V_{BAT}=4.1V	0.2	2.0	µs
V_{OUT} Dead Time, V_{DD} Falling (2)	t_{RSBF}	V_{BAT}=4.1V	0.2	2.0	µs
Bypass Resistance	R_{OUT}	-	-	2.5	Ω

(2) *Dead time is the time period when the V_{OUT} pin is floating. Size the holding capacitor accordingly.*

Note: All specifications contained within this document are subject to change without notice

Important timing diagrams for the EnerChip CC relationship between EnerChip Switchover Timing and EnerChip Disconnect from Load Timing are shown in Figure 4.

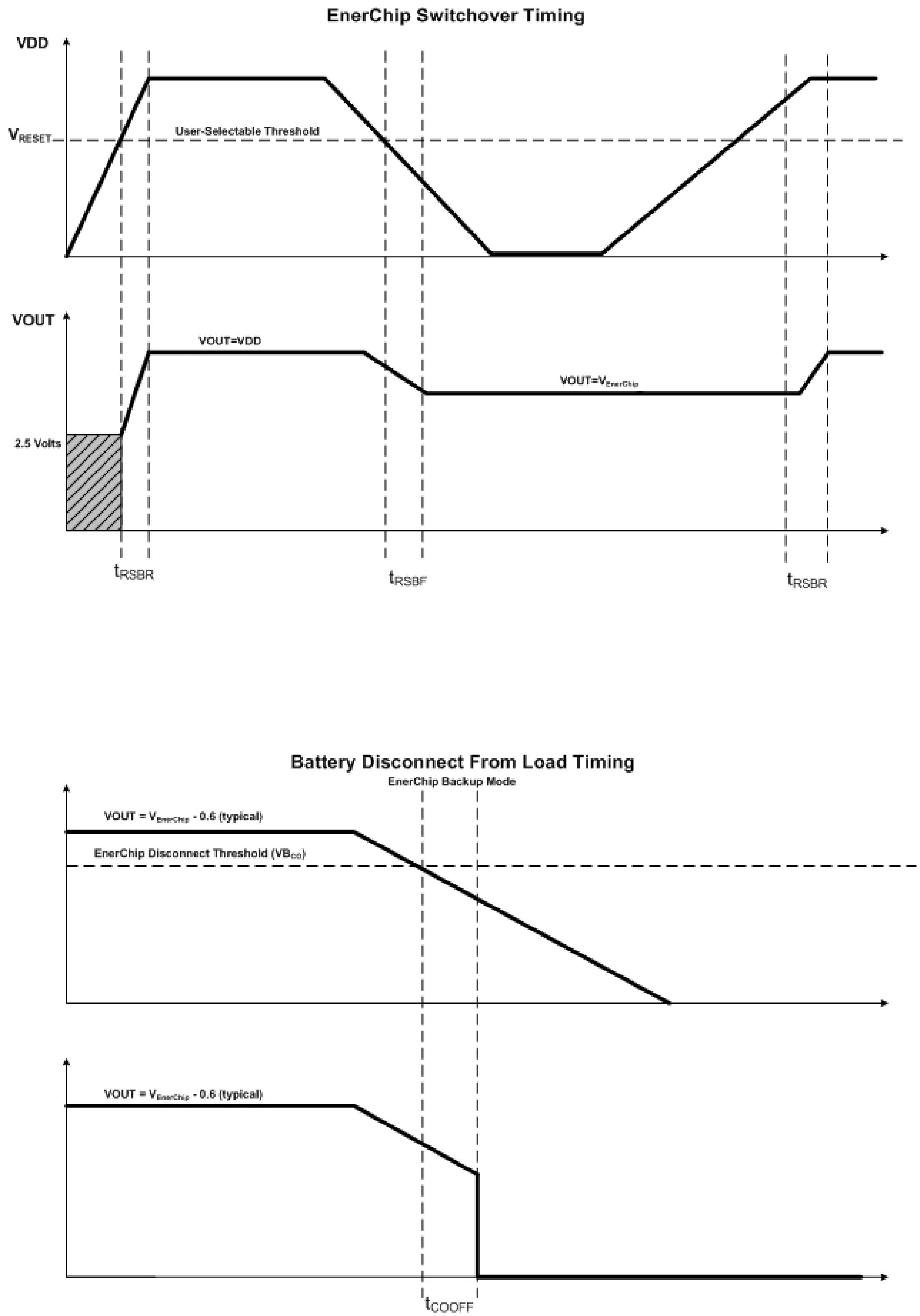


Figure 4: EnerChip CC Switchover and Disconnect Timing Diagrams

Timing diagrams for the EnerChip CC relationship between V_{DD} to $\overline{RESET}$ and ENABLE high to charge pump becoming active are shown in Figure 5.

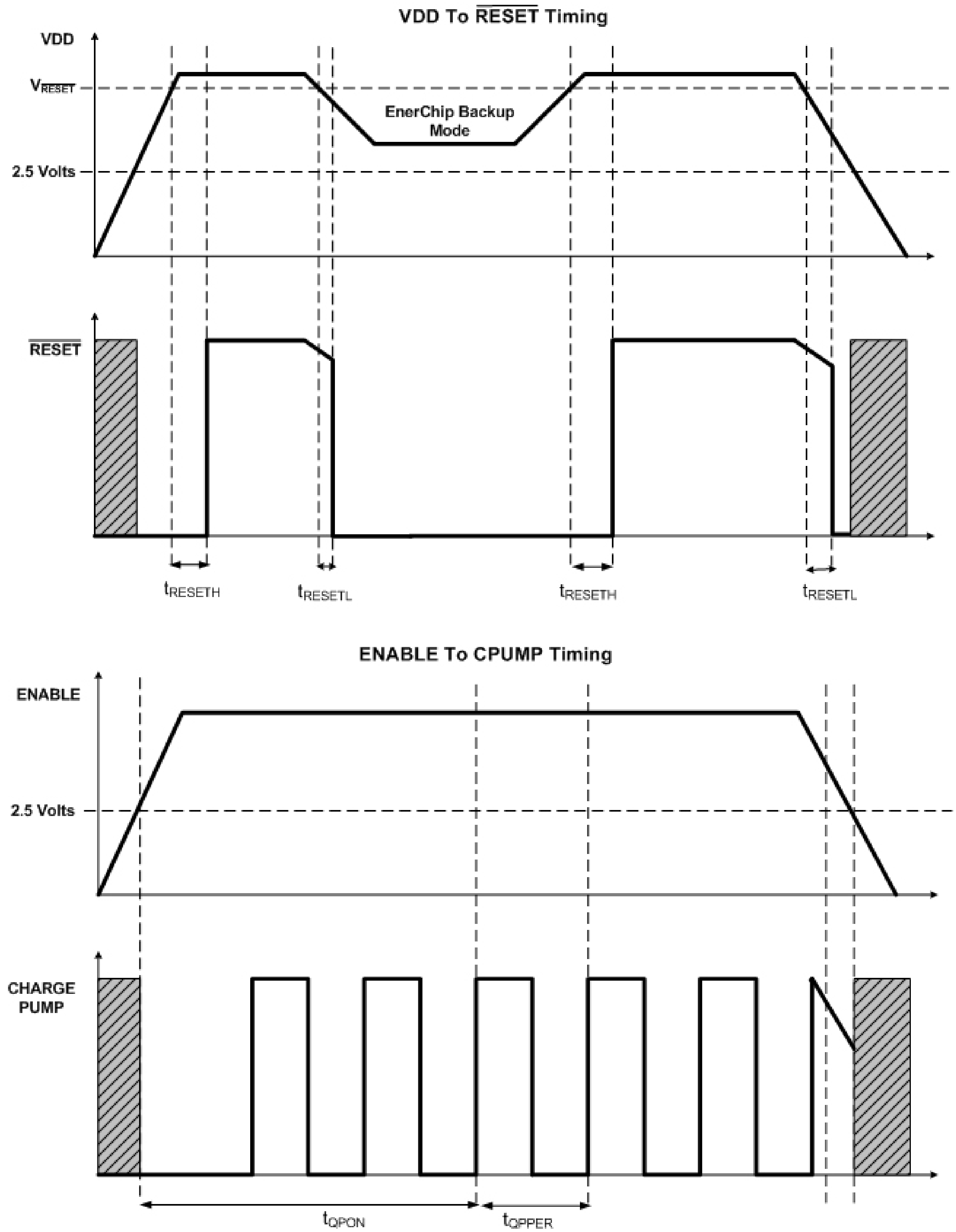


Figure 5: Timing Diagrams for V_{DD} to $\overline{RESET}$ and Enable to Charge Pump Active.

EnerChip CC Detailed Description

The EnerChip CC uses a charge pump to generate the supply voltage for charging the integrated energy storage device. An internal FET switch with low RDS_{ON} is used to route V_{DD} to V_{OUT} during normal operation when main power is above the switchover threshold voltage. When V_{DD} is below the switchover threshold voltage, the FET switch is shut off and V_{OUT} is supplied by the EnerChip. An interrupt signal is asserted low prior to the switchover.

Operating Modes

The EnerChip CC can be operated from various power supplies such as a primary source or a non-rechargeable battery. With the ENABLE pin asserted high, the charge pump is active and charges the integrated EnerChip. The EnerChip CC will be 80% charged within 10 minutes. Due to the rapid recharge it is recommended that, once the EnerChip CC is fully charged, the user de-assert the ENABLE pin (i.e., force low) to reduce power consumption. A signal generated from the MCU could be used to enable and disable the EnerChip CC.

When controlling the ENABLE pin by way of an external controller - as opposed to fixing the ENABLE line to VDD - ensure that the ENABLE pin is forced low by the controller anytime the $\overline{\text{RESET}}$ line is low, which occurs when the switchover threshold voltage is reached and the device is placed in backup mode. Although the internal charge pump is designed to operate below the threshold switchover level when the ENABLE line is active, it is recommended that the ENABLE pin be forced low whenever $\overline{\text{RESET}}$ is low to ensure no parasitic loads are placed on the EnerChip while in this mode. If ENABLE is high or floating while VDD is in an indeterminate state, bias currents within the EnerChip CC could flow, placing a parasitic load on the EnerChip that could dramatically reduce the effective backup operating time.

The EnerChip CC supports 2 operational modes as shown in Figures 6 and 7.

Mode 1 Operation

For use in 3.3 volt systems. The VMODE pin should be tied directly to GND, as shown in Figure 6. This will set the switchover threshold at approximately 3.0 volts.

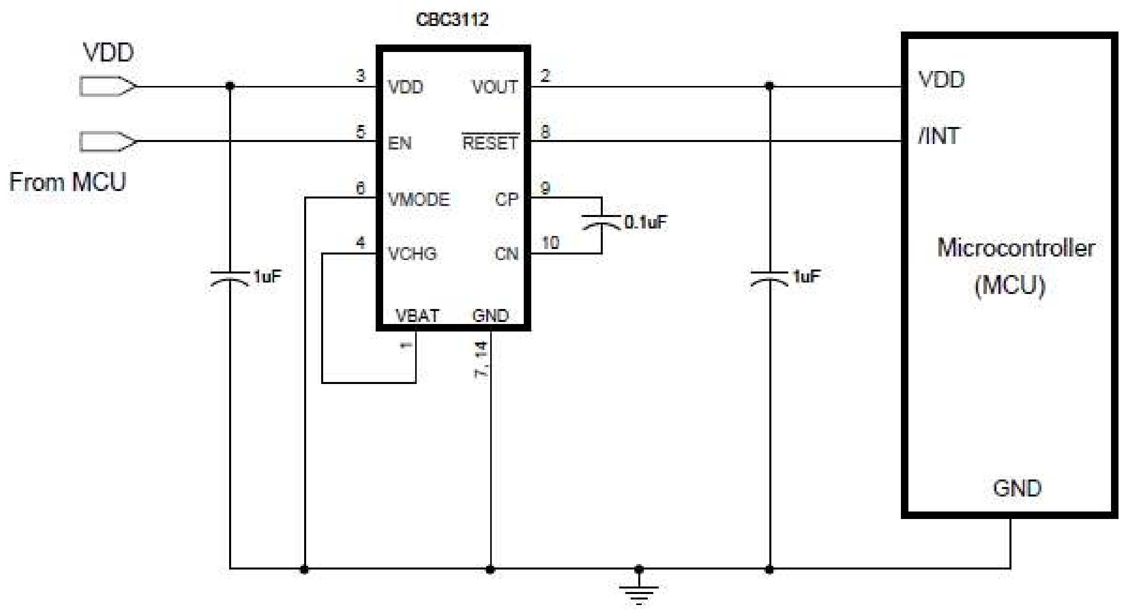


Figure 6: CBC3112 Typical Circuit for Mode 1 Operation

Mode 2 Operation

Figure 7 shows the circuitry for user-selectable switchover threshold to a value between 2.5 and 5.0 volts. Use Figure 8 to determine the value of R1. To determine the amount of hysteresis from the EnerChip switchover threshold, use Figure 9.

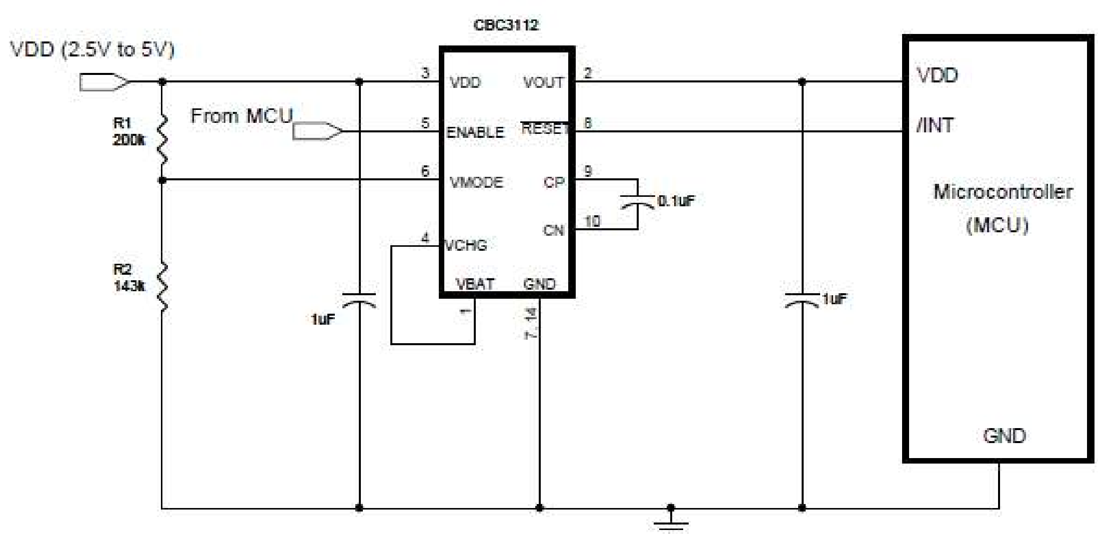


Figure 7: CBC3112 Typical Circuit for Mode 2 Operation

EnerChip charging and backup power switchover threshold for 2.5 to 5.5 volt operation is selected by changing the value of R2 (see Figure 7). To determine the backup switchover point, set the value of R1 to 200kΩ and choose the value of R2 according to Figure 8. For example, to set a 3.0V trip point: If R1=200 kΩ then R2 = R1 x 0.72 = 144kΩ. Figure 7 shows a Mode 2 circuit with standard value resistors of 200kΩ and 143kΩ.

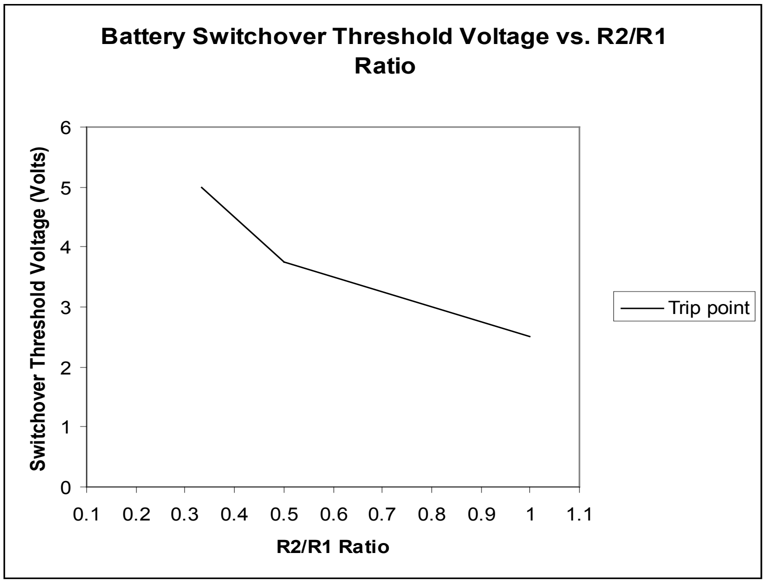


Figure 8: Mode 2 Resistor Selection Graph

To determine the backup switchover hysteresis for Mode 2 operation, use Figure 9.

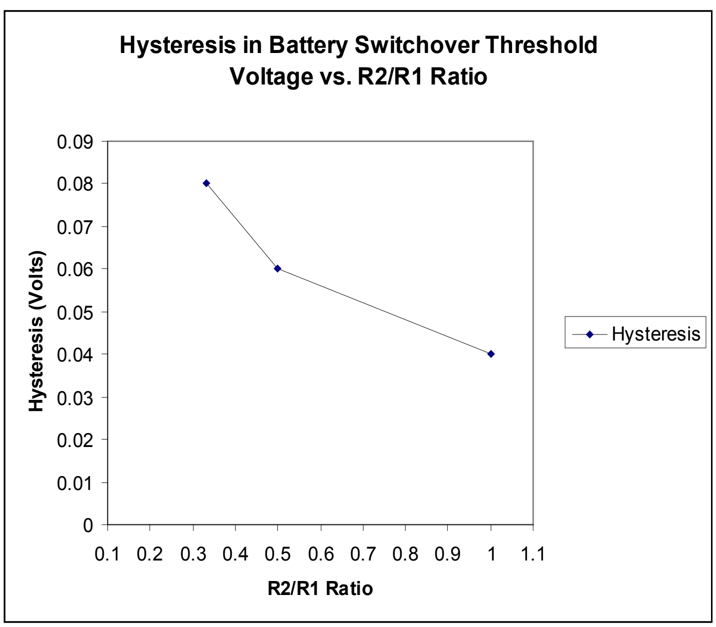


Figure 9: Mode 2 Hysteresis as a Function of R2/R1

Real-Time Clock Application Circuit

The EnerChip CC as depicted in Figure 10 is a typical application circuit in a 3.3 volt system where backup and power switchover circuitry for a real-time clock device is provided.

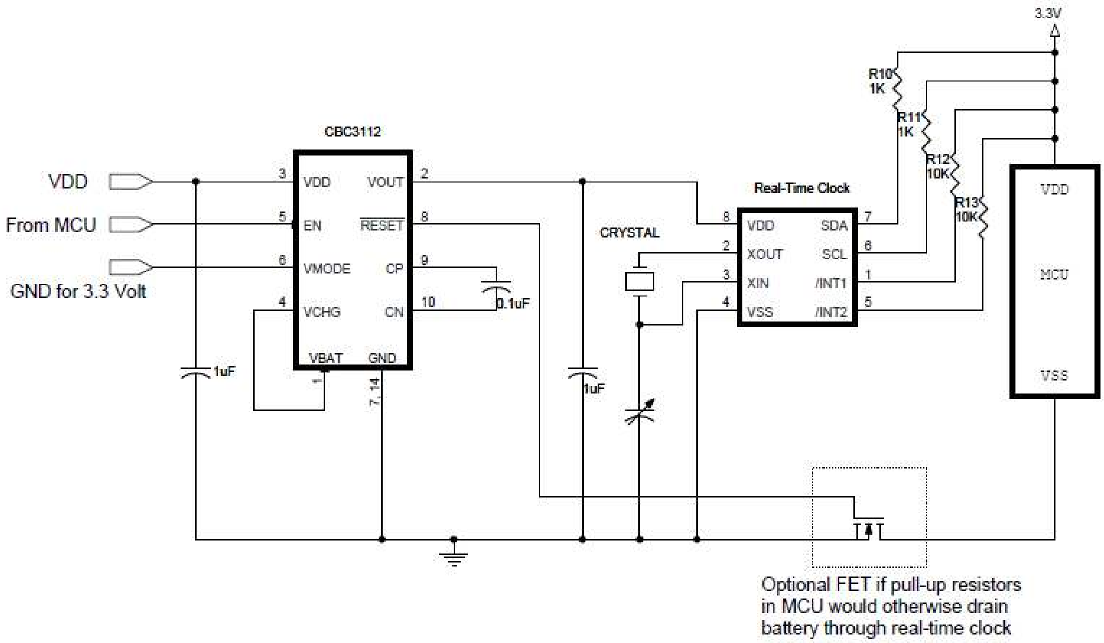


Figure 10: EnerChip CC Providing Real-Time Clock Backup Power

Adding Power and Energy Capacity with Parallel EnerChips

In some applications, additional EnerChip capacity might be needed. The schematic in Figure 11 shows how multiple EnerChips can be supported in parallel by a single EnerChip CC CBC3112. Note that C_{FLY} should be increased by 0.1μF for every additional EnerChip.

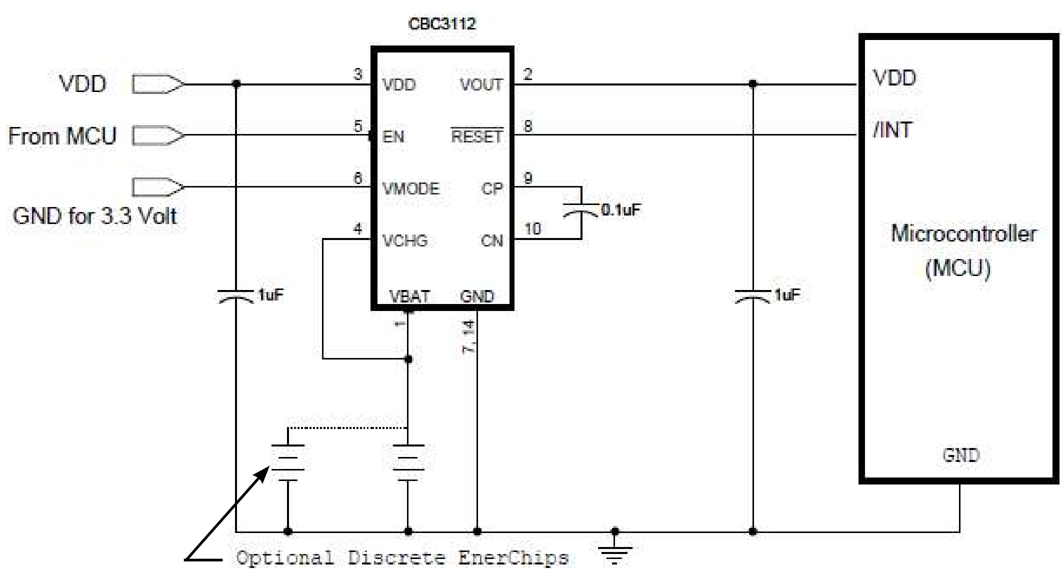


Figure 11: EnerChip CC Providing Power Management for Multiple EnerChips

EnerChip CC CBC3112 PCB Layout Guidelines - *Important Notice!*

There are several PCB layout considerations that must be taken into account when using the CBC3112:

1. All capacitors should be placed as close as possible to the EnerChip CC. The flying capacitor connections must be as short as possible and routed on the same layer the EnerChip CC is placed.
2. Power connections should be routed on the layer the EnerChip CC is placed.
3. A ground (GND) plane in the PCB should be used for optimal performance of the EnerChip CC.
4. Very low parasitic leakage currents from the VBAT pin to power, signal, and ground connections, can result in unexpected drain of charge from the integrated power source. Maintain sufficient spacing of traces and vias from the VBAT pin and any traces connected to the VBAT pin in order to eliminate parasitic leakage currents that can arise from solder flux or contaminants on the PCB.
5. Pin 1 VBAT and Pin 4 VCHG must be tied together for proper operation.
6. There should be no traces, vias or connections under the CBC3112 exposed die pad.
7. When placing a silk screen on the PCB around the perimeter of the package, place the silk screen outside of the package and all metal pads. Failure to observe this precaution can result in package cracking during solder reflow due to the silk screen material interfering with the solder solidification process during cooling.
8. See Figure 12 for location and dimensions of metal pad placement on the PCB.

Important Note: Designers using EnerChips in their products should also download the EnerChip User Manual Application Note AN-1026 found here: http://www.cymbet.com/products/datasheets-downloads.php.

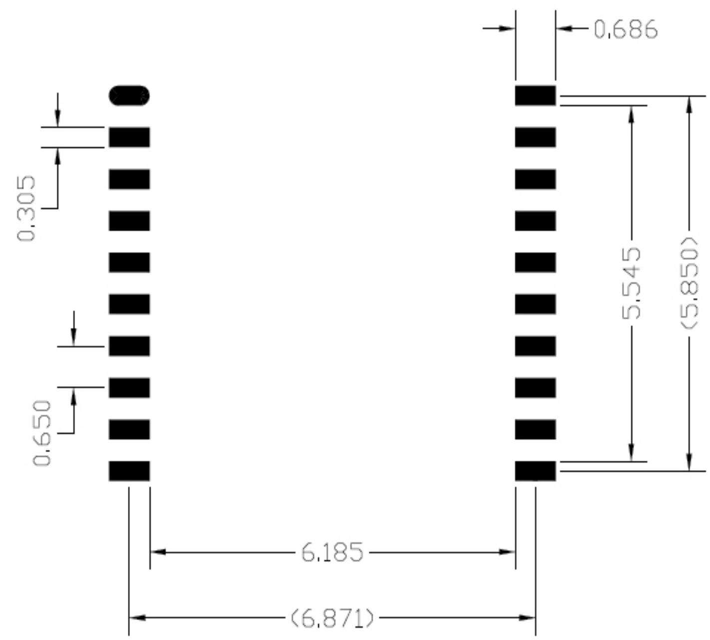
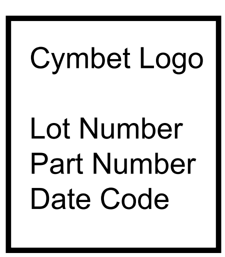
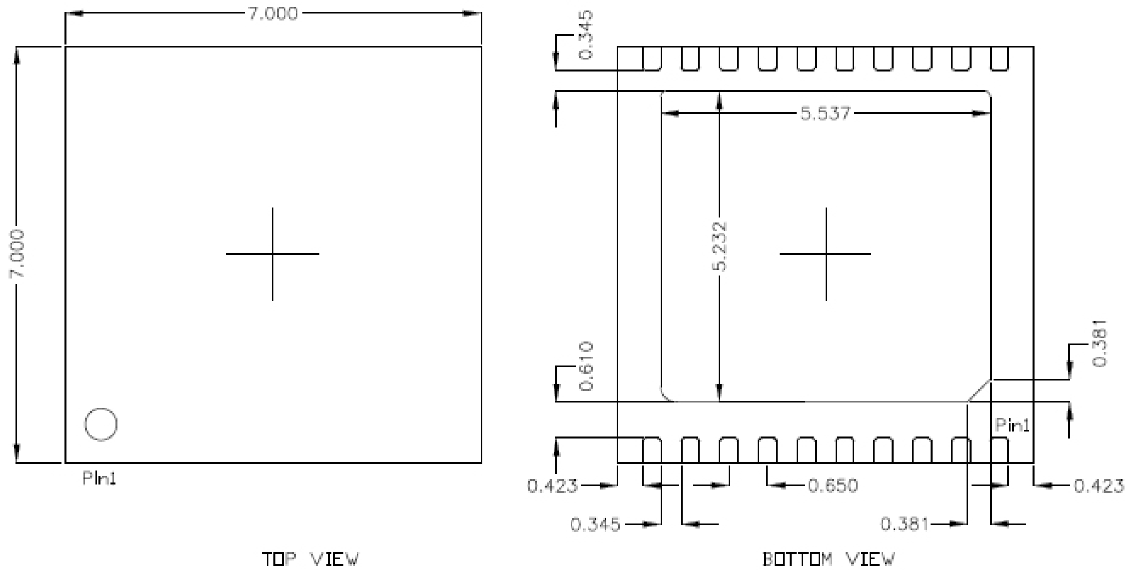


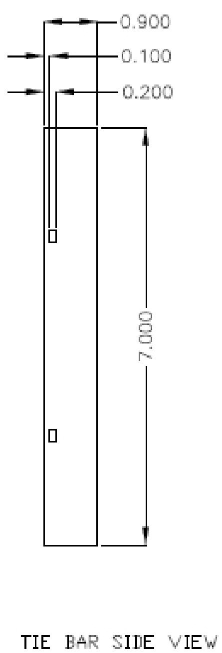
Figure 12: Recommend PCB Layout for the CBC3112-D7C Package (Dimensions in mm)

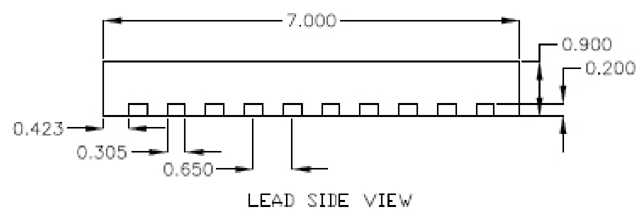


CBC3112 Labeling Information Placement

CBC3112 7mm x 7mm DFN Package Drawing and Dimensions







Notes:
1. Dimensions in millimeters.
2. Package dimensions do not include mold flash, protrusions, burrs or metal smearing.
3. Coplanarity applies to the exposed pad as well as the exposed terminals. Maximum coplanarity shall be 0.08. Warpage shall not exceed 0.10.
4. Refer to JEDEC MO-229 outline.
5. Exposed metallized feature connected to die paddle.
6. There are 10 contact pads on two opposite sides and no contact pads on the other two sides.

Handling EnerChips as MSL 3 Devices

EnerChip CBC050 devices are rated Moisture Sensitivity Level 3 and must be mounted and reflowed within 168 hours of being removed from the moisture barrier antistatic bag.

Soldering, Rework, and Electrical Test

Refer to the Cymbet User Manual AN-1026 for soldering, rework, and replacement of the EnerChip on printed circuit boards, and for instructions on in-circuit electrical testing of the EnerChip.

Energy Harvesting with the EnerChip CC

The EnerChip CC can be configured to collect energy from transducers such as low power photovoltaic (PV) cells and use that harvested energy to charge the integrated EnerChip and deliver self-sustaining power to components such as microcontrollers, sensors, and radios in wireless systems. The schematic of Figure 13 illustrates the feedback connection made from RESET to EN to implement the energy harvesting function with the CBC3150. In order to make most efficient use of the power available from the transducer (for example, a PV cell), it is necessary to know the electrical characteristics including voltage and peak power point of the transducer being used. For assistance in designing your system to effectively harvest energy from a power transducer in a specific environment, contact Cymbet Applications Engineering.

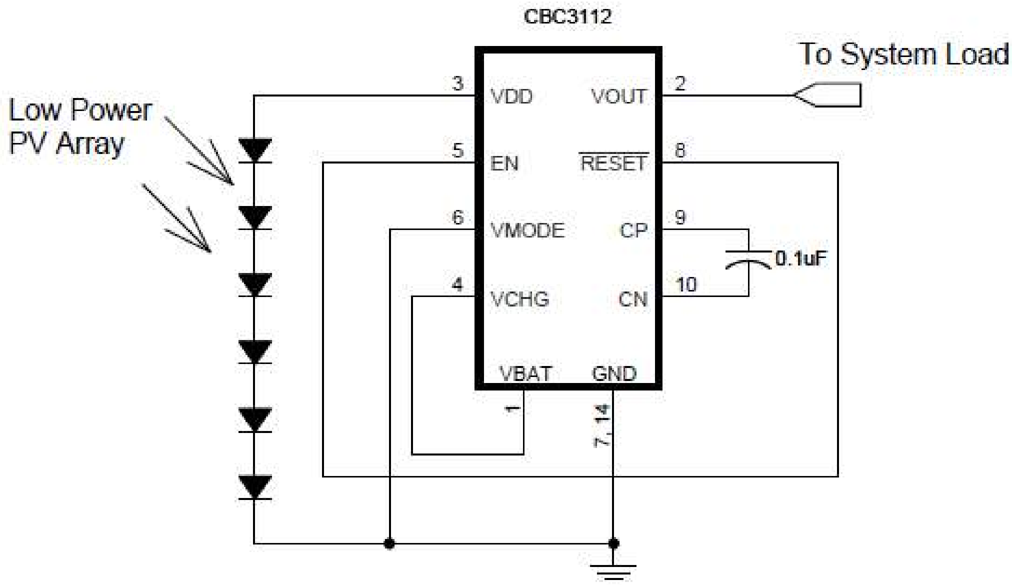


Figure 13: Implementing Energy Harvesting with the EnerChip CC

Ordering Information - available for Last Time Buy until September 12, 2014

EnerChip CC Part Number	Description	Notes
CBC3112-D7C	EnerChip CC 12µAh in 20-pin D7 DFN Package	Shipped in Tube
CBC3112-D7C-TR1 CBC3112-D7C-TR5	EnerChip CC 12µAh in 20-pin D7 DFN Package	Tape-and-Reel - 1000 pcs (TR1) or 5000 pcs (TR5) per reel
CBC3112-D7C-WP	EnerChip CC 12µAh in 20-pin D7 DFN Package	Waffle Pack

U.S. Patent No. 8,044,508. Additional U.S. and Foreign Patents Pending